

Abstract

Method for fabricating a transistor structure

The invention relates to a method for fabricating a transistor structure, comprising at least a first and a second bipolar transistor having different collector widths.

The invention is distinguished by the fact that all junctions between differently doped regions have a sharp interface. In this case, by way of example, a first collector region 2.1 is suitable for a high-frequency transistor with high limiting frequencies  $f_T$  and a second collector region 2.2 is suitable for a high-voltage transistor with increased breakdown voltages.

Figure 3c